

SANYO Semiconductors

DATA SHEET

An ON Semiconductor Company

N-Channel Silicon MOSFET

2SK3748— High-Voltage, High-Speed Switching **Applications**

Features

- · Low ON-resistance, low input capacitance, ultrahigh-speed switching
- High reliability (Adoption of HVP process)
- · Attachment workability is good by Mica-less package
- · Avalanche resistance guarantee

Specifications

Absolute Maximum Ratings at Ta=25°C

0				
Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	VDSS		1500	V
Gate-to-Source Voltage	VGSS		±20	V
Drain Current (DC)	ID*		4	А
Drain Current (Pulse)	IDP	PW≤10µs, duty cycle≤1%	8	А
Allowable Power Dissipation			3.0	W
	PD	Tc=25°C	65	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		-55 to +150	°C
Avalanche Energy (Single Pulse) *1	EAS		165	mJ
Avalanche Current *2	IAV		4	А

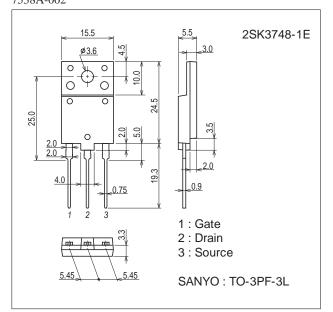
*Shows chip capability

*1 VDD=50V, L=20mH, IAV=4A (Fig.1)

*2 L≤20mH, single pulse

Package Dimensions

unit : mm (typ) 7538A-002



Product & Package Information

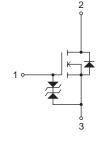
: TO-3PF-3L • Package

- : SC-94 • JEITA, JEDEC
- Minimum Packing Quantity : 30 pcs./magazine

Marking

Electrical Connection





SANYO Semiconductor Co., Ltd. http://semicon.sanyo.com/en/network

52312 TKIM TC-00002764/72905 MSIM TB-00001688 / 31005QB TSIM TB-00001272 No.8250-1/7

Electrical Characteristics at Ta=25°C

Parameter	Symbol Conditions		Ratings			1.1	
Parameter	Symbol	Symbol Conditions		typ	max	- Unit	
Drain-to-Source Breakdown Voltage	V(BR)DSS	ID=1mA, VGS=0V	1500			V	
Zero-Gate Voltage Drain Current	IDSS	V _{DS} =1200V, V _{GS} =0V			100	μΑ	
Gate-to-Source Leakage Current	IGSS	V _{GS} =16V, V _{DS} =0V			±10	μΑ	
Cutoff Voltage	VGS(off)	V _{DS} =10V, I _D =1mA	2.5		3.5	V	
Forward Transfer Admittance	yfs	VDS=20V, ID=2A	1.7	2.8		S	
Static Drain-to-Source On-State Resistance	R _{DS} (on)	ID=2A, VGS=10V		5	7	Ω	
Input Capacitance	Ciss			790		pF	
Output Capacitance	Coss	V _{DS} =30V, f=1MHz		140		pF	
Reverse Transfer Capacitance	Crss			70		pF	
Turn-ON Delay Time	t _d (on)			17		ns	
Rise Time	tr			75		ns	
Turn-OFF Delay Time	t _d (off)	See Fig.2		360		ns	
Fall Time	tf			116		ns	
Total Gate Charge	Qg			80		nC	
Gate-to-Source Charge	Qgs	V _{DS} =200V, V _{GS} =10V, I _D =4A		6.4		nC	
Gate-to-Drain "Miller" Charge	Qgd	1		36		nC	
Diode Forward Voltage	V _{SD}	I _S =4A, V _{GS} =0V 0.94 1		1.2	V		
Reverse Recovery Time	trr	IS=4A, VGS=0V, dis/dt=100A/µs		340		ns	

Fig.1 Avalanche Resistance Test Circuit

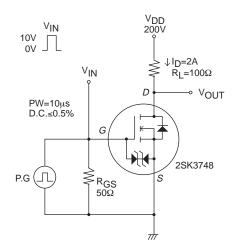
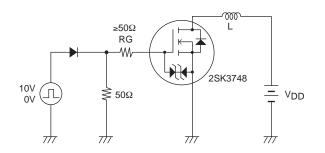


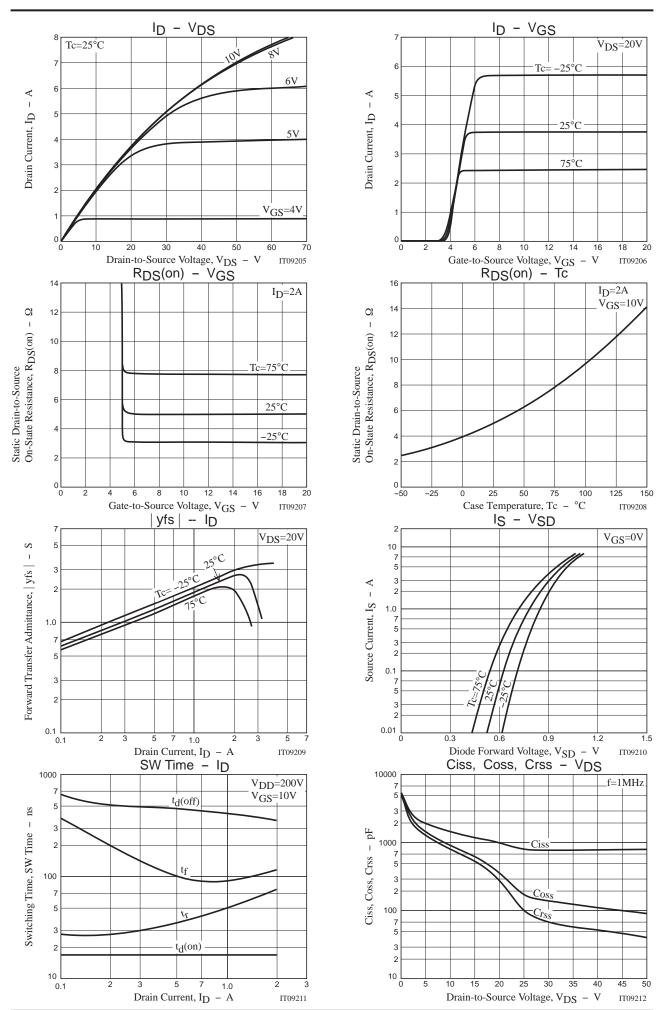
Fig.2 Switching Time Test Circuit

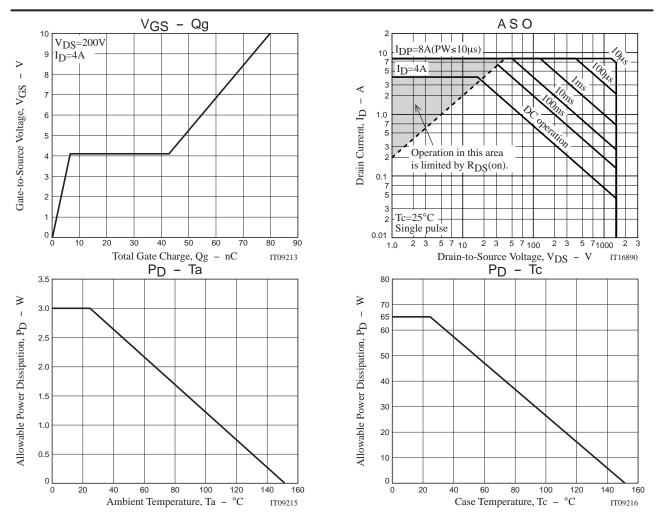


Ordering Information

Device	Package	Shipping	memo	
2SK3748-1E	TO-3PF-3L	30pcs./magazine	Pb Free	

2SK3748





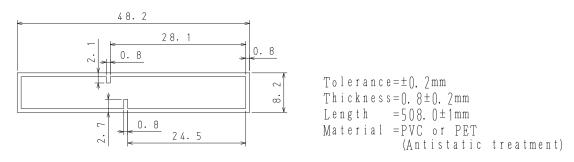
Magazine Specification 2SK3748-1E

1. Packing Format

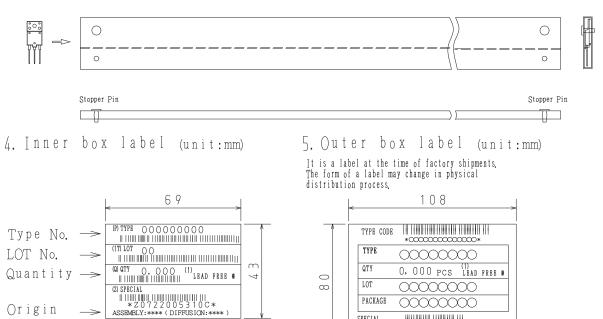
Package Name	Maximum Number of devices contained (pcs)			Packing format		
I gouge o Hamo	Magazine	Inner box	Outer box	Inner BOX	Outer BOX	
TO-3PF-3L	30	360	1440	12 magazines contained Dimensions:mm (external)	SPD-LV0010 4 inner boxes contained Dimensions:mm (external) 590x225x178	

2. Magazine dimensions

(unit:mm)



3. Storage method to magazine

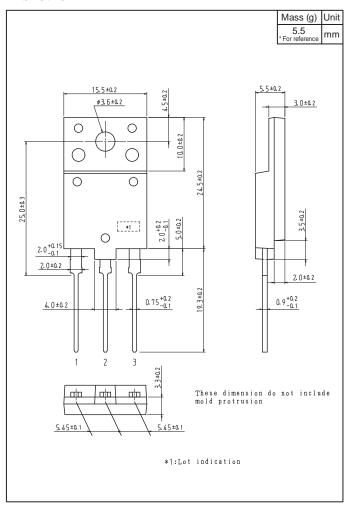


SPECIAL

L SPECIAL * Z O 7 Z 2 O O 5 3 1 O C * ASSEMBLY:**** (DIFFUSION:****) NOTE (1) The LEAD FREE * description shows that the surface treatment of the terminal is lead free.

Label		JEITA Phase
LEAD FREE	3	JEITA Phase 3A

Outline Drawing 2SK3748-1E



Note on usage : Since the 2SK3748 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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